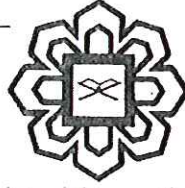


Name: \_\_\_\_\_

Matric No: \_\_\_\_\_ Section: \_\_\_\_\_



الجامعة الإسلامية العالمية ماليزيا

INTERNATIONAL ISLAMIC UNIVERSITY MALAYSIA

MID-TERM EXAMINATION  
SEMESTER I, 2012/2013 SESSION  
KULLIYAH OF ENGINEERING

Programme : ENGINEERING Level of Study : UG 2  
Time : 8:00pm-10:00 pm Date : 19/10/2012  
Duration : 2 Hours  
Course Code : ECE 2133 Section(s) : 1 & 2  
Course Title : **Electronic Circuits**

This Question Paper consists of **Nine (9)** Printed Pages (Including Cover and a blank page) with **Three (3)** Questions.

**INSTRUCTION(S) TO CANDIDATES**

DO NOT OPEN UNTIL YOU ARE ASKED TO DO SO

- Use only pen for writing answer.
- Do not use your own sheet.
- Useful formulas are given in page 9.
- A total mark of this examination is 60.
- This examination is worth 30% of the total assessment.
- For drawing you may use pencil
- Answer **ALL THREE(3)** questions.

**Any form of cheating or attempt to cheat is a serious offence which may lead to dismissal.**

	Question 1	Question 2	Question 3	Total Marks
Marks	20	20	20	60
Marks Obtained				

**Q.1 [20 marks]**

- (a) Determine the Q-point values ( $I_{DQ}$  and  $V_{DSQ}$ ) for the circuit shown in Fig. 1(a). The transistor parameters are  $V_{TN} = 0.8$  V,  $K_n = 2 \text{ mA/V}^2$  and  $\lambda = 0$ . The circuit parameters are  $V_{DD} = 12$  V,  $R_S = 1$  k $\Omega$ ,  $R_1 = 225$  k $\Omega$ ,  $R_2 = 175$  k $\Omega$ ,  $R_D = 2$  k $\Omega$  and  $R_L = 10$  k $\Omega$ ,  $C_{C1} = C_{C2} = 10$   $\mu\text{F}$ . Also calculate small signal circuit parameters.

(10 marks)

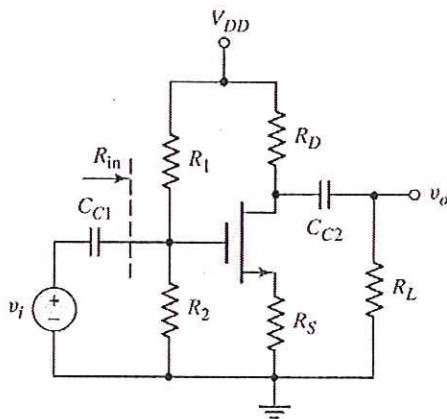
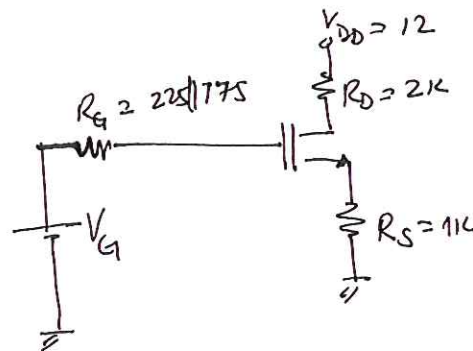


Fig. 1(a)



$$R_g = R_1 \parallel R_2 = 225 \parallel 175 = 98.4375 \text{ k}\Omega$$

$$V_g = \frac{12 \times 175}{225 + 175} = 5.25 \text{ V} \leftarrow$$

KVL:

$$V_g = I_D R_g + V_{GS} + I_D R_S$$

$$= V_{GS} + I_D R_S = V_{GS} + K_n (V_{GS} - V_T)^2 R_S$$

[  $\because I_D = K_n (V_{GS} - V_T)^2$  ]  
considering sat'n.

$$\therefore 5.25 = V_{GS} + 2 (V_{GS} - 0.8)^2 \times 1 = V_{GS} + 2V_{GS}^2 - 2 \times 2 \times 0.8 V_{GS} + 2 \times 0.64$$

$$\Rightarrow 2V_{GS}^2 - 2.2V_{GS} - 3.97 = 0 \quad \therefore V_{GS1} = 2.062 \text{ V}$$

$$V_{GS2} = -0.96 \text{ V}$$

Consider  $V_{GSQ} = 2.062 \text{ V} \geq V_T$

$$\therefore I_{DQ} = K_n (V_{GSQ} - V_T)^2 = 2 (2.062 - 0.8)^2 = 3.185 \text{ mA} \leftarrow$$

$$V_{DSQ} = V_{DD} - I_D (R_D + R_S) = 12 - 3.185 (2 + 1) = 2.444 \text{ V} \leftarrow$$

$$g_m = 2 \sqrt{K_n I_{DQ}} = 2 \sqrt{2 \times 3.185} = 5.05 \text{ mA/V}$$

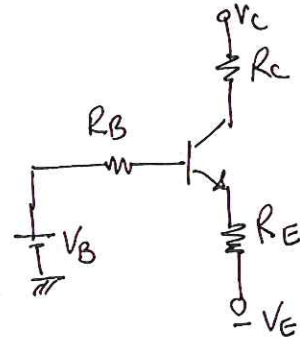
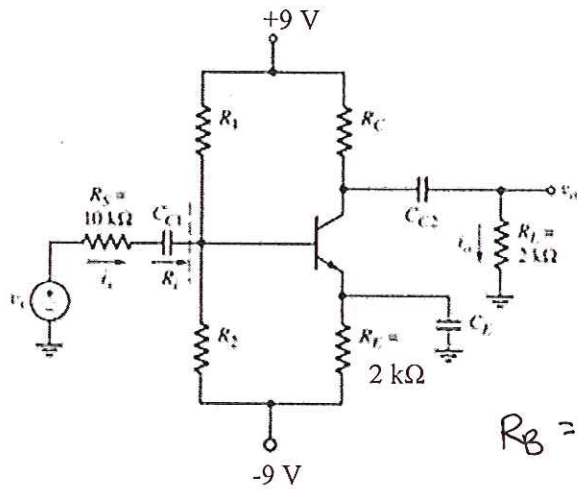
$$r_o = \frac{1}{\lambda I_{DQ}} = \infty \quad \leftarrow$$

$$V_{DS} = 2.444 \text{ V}$$

$$V_{GS} - V_T = 2.062 - 0.8$$

Saturation Region

(b) For the circuit shown in Fig 1(b), design a bias stable circuit such that  $I_{CQ} = 0.8$  mA and  $V_{CEQ} = 1.0$  V assuming  $\beta = 120$  and  $V_A = 100$  and hence find small signal parameters  $g_m$ ,  $r_\pi$  and  $r_o$ . (10 marks)



$R_B = 0.1(1+\beta) R_E$  for stable bias  
 $= 0.1 \times 121 \times 22 = 24.2 \text{ k}\Omega$

Fig. 1 (b)

KVL

$$V_C = I_C R_C + V_{CE} + I_E R_E - V_E = I_C R_C + \frac{(1+\beta)}{\beta} I_C R_E$$

$$V_C + V_E - V_{CE} = I_C R_C + I_E R_E = I_C R_C + \frac{(1+\beta)}{\beta} I_C R_E$$

$$\therefore I_C R_C = (V_C + V_E - V_{CE}) - \frac{(1+\beta)}{\beta} I_C R_E$$

$$= (9+9-1) - \frac{121}{120} \times 0.8 \times 2 = 15.3867 \text{ V}$$

$$\therefore R_C = \frac{15.3867}{0.8} = 19.233 \text{ k}\Omega$$

KVL

$$V_B = I_B R_B + V_{BE} + I_E R_E - V_E = \frac{I_C}{\beta} R_B + V_{BE} + \frac{(1+\beta)}{\beta} I_C R_E - V_E$$

$$= \frac{0.8}{120} \times 24.2 + 0.7 + \frac{121}{120} \times 0.8 \times 2 - 9 = -6.525 \text{ V}$$

again,  $V_B = \frac{(V_{CC} + V_E) R_2}{R_1 + R_2} - V_E = \frac{R_B}{R_1} (V_{CC} + V_E) - V_E$

$$-6.525 = \frac{24.2}{R_1} (9+9) - 9 \Rightarrow R_1 = 176.26 \text{ k}\Omega$$

$$\frac{1}{R_B} = \frac{1}{R_1} + \frac{1}{R_2} \Rightarrow R_2 = 28.05 \text{ k}\Omega$$

$$g_m = \frac{I_{CQ}}{V_T} = \frac{0.8 \text{ mA}}{0.026} = 30.77 \text{ mA/V}$$

$$r_o = \frac{V_A}{I_{CQ}} = \frac{100}{0.8} = 125 \text{ k}\Omega$$

$$r_\pi = \frac{\beta}{g_m} = \frac{120}{30.77} = 3.9 \text{ k}\Omega$$

**Q.2 [20 marks]**

(a) Draw the small signal equivalent circuit diagram of the circuit shown in Fig. 2(a)

and find the input resistance  $R_i$  and the voltage gain  $A_v = \frac{v_o}{v_s}$  of the amplifier.

Given that  $R_s=0.5 \text{ k}\Omega$ ,  $R_1=330 \text{ k}\Omega$ ,  $R_2=85 \text{ k}\Omega$ ,  $R_C = 4 \text{ k}\Omega$ ,  $R_E=1.5 \text{ k}\Omega$ , and  $I_{CQ} = 0.4 \text{ mA}$ . Transistor parameters are  $\beta=100$  and  $V_A = \infty$ . (10 marks)

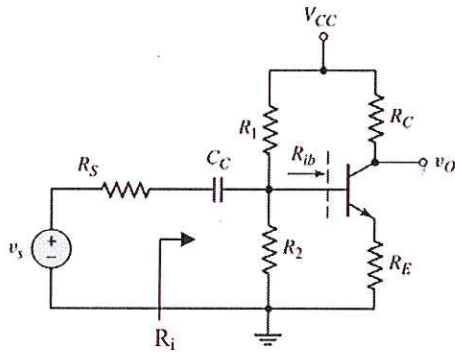
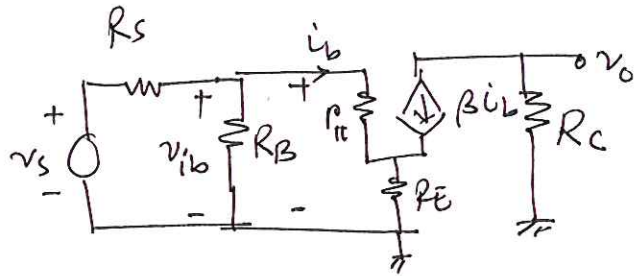


Fig. 2(a)



$$v_o = -\beta i_b R_C$$

$$v_{ib} = r_{\pi} i_b + (1+\beta) i_b R_E$$

$$= [r_{\pi} + (1+\beta) R_E] i_b$$

$$r_{\pi} = \frac{\beta V_T}{I_{CQ}} = \frac{100 \times 0.026}{0.4}$$

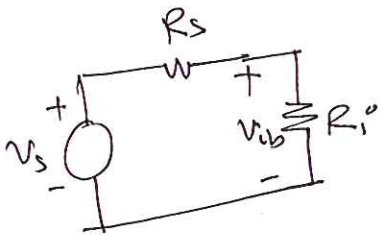
$$= 6.5 \text{ k}\Omega$$

$$\therefore R_{ib} = \frac{v_{ib}}{i_b} = r_{\pi} + (1+\beta) R_E$$

$$= 6.5 + (1+100) \times 1.5 = 158 \text{ k}\Omega \leftarrow$$

$$R_i = R_1 \parallel R_2 \parallel R_{ib} = 330 \parallel 85 \parallel 158$$

$$= 47.34 \text{ k}\Omega$$



$$\frac{v_{ib}}{v_s} = \frac{R_i}{R_s + R_i} = \frac{47.34}{0.5 + 47.34} = 0.989$$

$$v_o = -\frac{\beta R_C v_{ib}}{R_{ib}}$$

$$\therefore A_{vA} = \frac{v_o}{v_{ib}} = -\frac{\beta R_C}{R_{ib}}$$

$$= -\frac{100 \times 4}{158} = -2.5316$$

$$\therefore A_v = \frac{v_o}{v_s} = A_{vA} \times \frac{v_{ib}}{v_s}$$

$$= A_{vA} \times \frac{R_i}{R_s + R_i} = -2.504 \leftarrow$$

(b) Draw the small signal equivalent circuit diagram of the circuit shown in Fig. 2(b)

and find the voltage gain  $A_v = \frac{v_o}{v_i}$  and output resistance  $R_o$  of the amplifier.

Given that  $R_{Si} = 2 \text{ k}\Omega$ ,  $R_1 = 180 \text{ k}\Omega$ ,  $R_2 = 330 \text{ k}\Omega$ ,  $R_S = 1.0 \text{ k}\Omega$  and  $I_D = 6 \text{ mA}$ . The transistor parameters are  $V_{TN} = 1.5 \text{ V}$ ,  $K_n = 4 \text{ mA/V}^2$  and  $\lambda = 0.01 \text{ V}^{-1}$ . (10 marks)

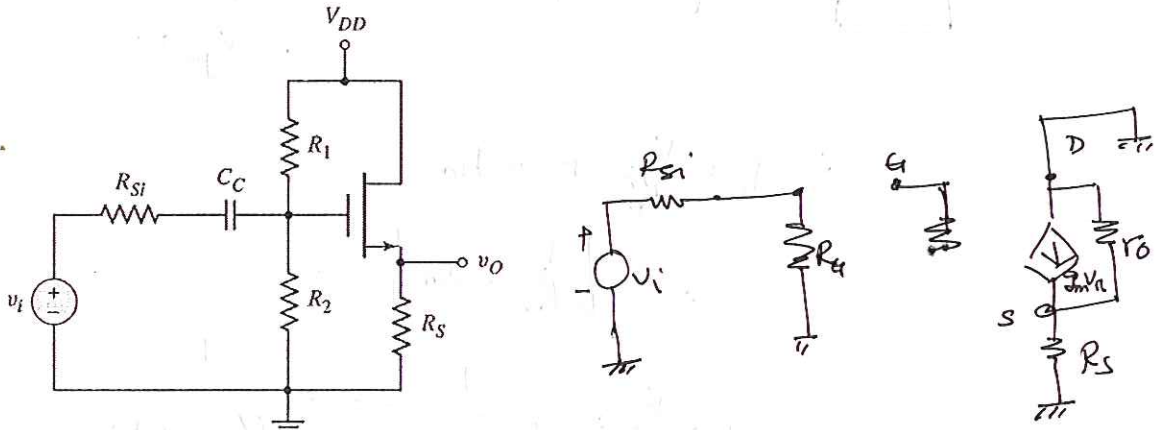
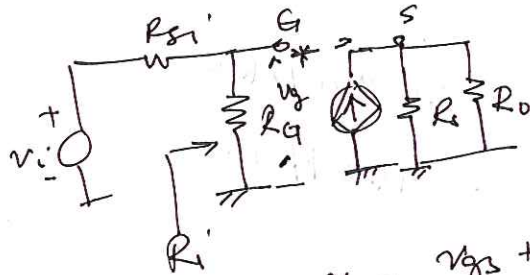


Fig. 2(b)



$$R_L = R_D \parallel R_S =$$

$$v_o = g_m v_{gs} R_L$$

$$v_g = v_{gs} + g_m v_{gs} R_L' = v_{gs} (1 + g_m R_L')$$

$$\therefore v_{gs} = \frac{v_g}{1 + g_m R_L'}$$

$$\therefore v_o = g_m v_{gs} R_L' = \frac{g_m R_L'}{1 + g_m R_L'} v_g$$

$$A_{v_A} = \frac{v_o}{v_g} = \frac{g_m R_L'}{1 + g_m R_L'}$$

$$R_G = R_1 \parallel R_2 = 180 \parallel 330 = 116.47 \text{ k}\Omega$$

$$g_m = 2\sqrt{K_n I_{DQ}} = 2\sqrt{4 \times 6} = 9.79 \approx 9.8 \text{ mA/V}$$

$$r_o = \frac{1}{\lambda I_{DQ}} = \frac{1}{0.01 \times 6} = 16.67 \text{ k}\Omega$$

$$-i R_L = 10 \parallel R_S = 0.943 \text{ k}\Omega$$

$$\therefore g_m R_L' = 9.245$$

$$A_v = \frac{v_o}{v_i} = A_{v_A} \times \frac{R_i}{R_i + R_{Si}} = \frac{g_m R_L'}{1 + g_m R_L'} \times \frac{R_G}{R_G + R_{Si}} = \frac{9.245}{1 + 9.245} \times \frac{116.47}{116.47 + 2} = 0.902 \times 0.983 = 0.887$$

**Q.3 [20 marks]**

(a) Draw the small signal equivalent circuit diagram of the circuit shown in Fig. 3(a).

(6 marks)

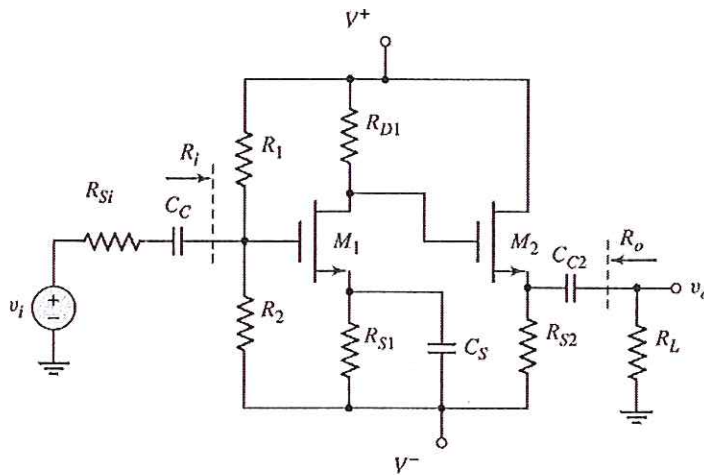
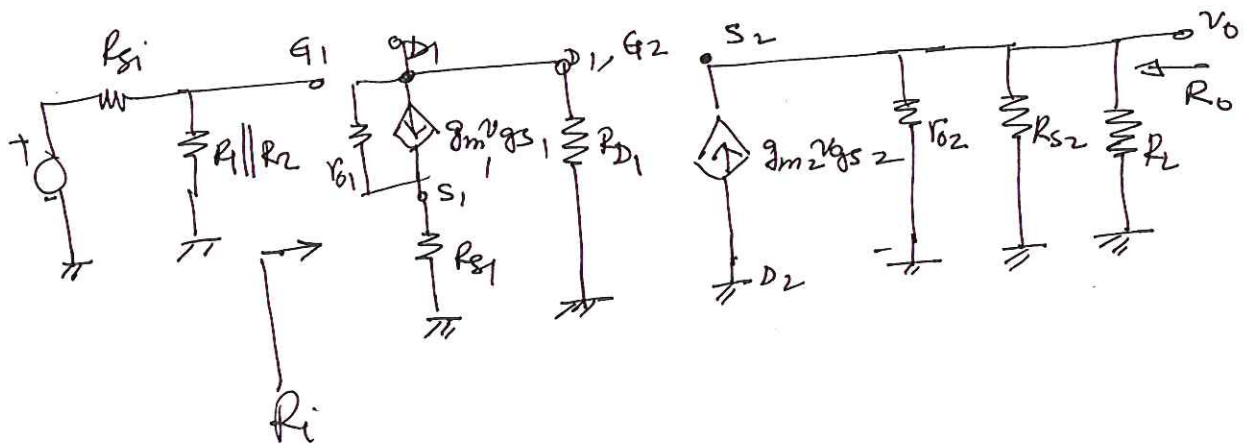
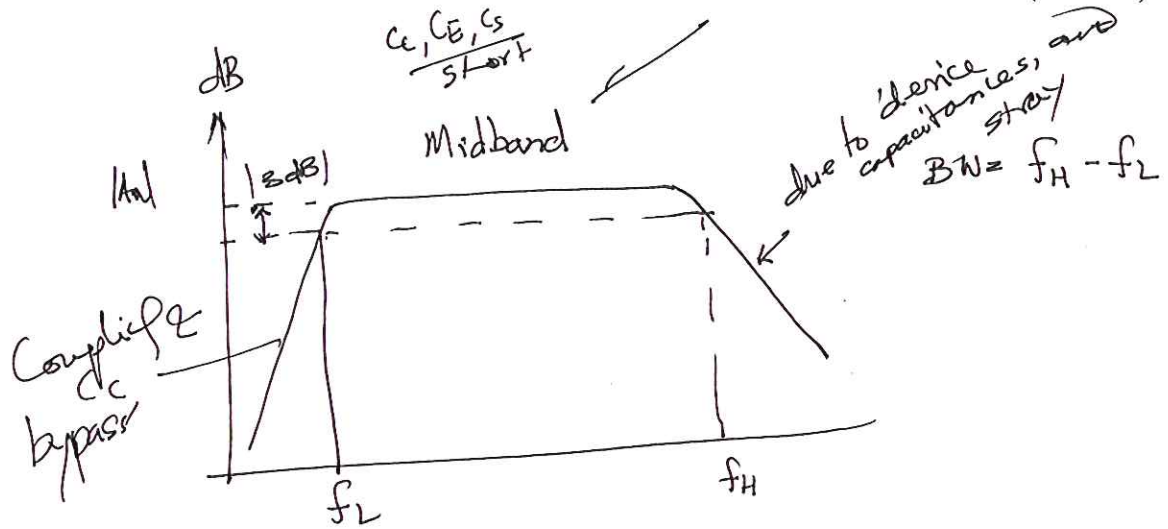


Fig. 3(a)



(b) Draw the typical frequency response of an amplifier and explain its behavior.

(6 marks)



- (c) Consider the circuit shown in Fig. 3(c), derive the expression for the voltage transfer function  $T(s) = v_o(s)/v_i(s)$ . Put expression in the form of  $T(s) = K(1 + s\tau_A)/(1 + s\tau_B)$ . What are the values of  $K$ ,  $\tau_A$  and  $\tau_B$ ? (8 marks)

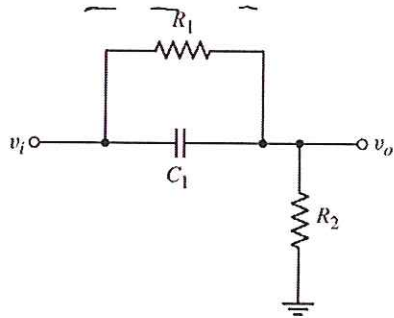
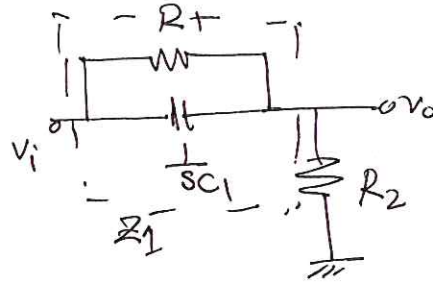


Fig. 3(c)



$$Z_1 = R_1 \parallel \frac{1}{sC_1} = \frac{R_1 \times \frac{1}{sC_1}}{R_1 + \frac{1}{sC_1}} = \frac{R_1}{1 + sC_1 R_1}$$

$$\frac{V_o}{V_i} = \frac{R_2}{R_2 + \frac{R_1}{1 + sC_1 R_1}} = \frac{R_2 (1 + sC_1 R_1)}{R_2 (1 + sC_1 R_1) + R_1}$$

$$= \frac{R_2 (1 + sC_1 R_1)}{R_1 + R_2 + sC_1 R_1 R_2} = \frac{R_2}{R_1 + R_2} \cdot \frac{(1 + sC_1 R_1)}{\left(1 + sC_1 \frac{R_1 R_2}{R_1 + R_2}\right)}$$

$$= K \cdot \frac{1 + s\tau_A}{1 + s\tau_B}$$

Therefore  $K = \frac{R_2}{R_1 + R_2}$  ←

$$\tau_A = C_1 R_1$$
 ←

$$\tau_B = R_1 \parallel R_2 = \frac{R_1 R_2}{R_1 + R_2}$$
 ←



**Useful formulas****For BJT**For bias stable  $R_B = 0.1(1 + \beta)R_E$ 

$$g_m = \frac{I_{CQ}}{V_T}$$

$$r_\pi = \frac{\beta V_T}{I_{CQ}}$$

$$r_o = \frac{V_A}{I_{CQ}}$$

$$V_T = 0.026 \text{ V}$$

$$V_{BE} = 0.7 \text{ V}$$

**For MOSFET**

$$g_m = 2\sqrt{k_n I_{DQ}}$$

$$r_o = \frac{1}{\lambda I_{DQ}}$$